2-Input Exclusive OR Gate

The MC74VHC1G86 is an advanced high speed CMOS 2–input Exclusive OR gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The MC74VHC1G86 input structure provides protection when voltages up to 7V are applied, regardless of the supply voltage. This allows the MC74VHC1G86 to be used to interface 5V circuits to 3V circuits.

- High Speed: $t_{PD} = 3.5$ ns (Typ) at $V_{CC} = 5V$
- Low Power Dissipation: $I_{CC} = 2\mu A$ (Max) at $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; MM > 200V, CDM > 1500V

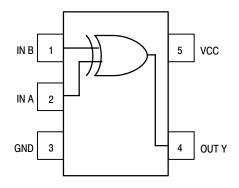


Figure 1. 5-Lead SOT-353 Pinout (Top View)

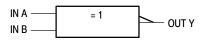


Figure 2. Logic Symbol

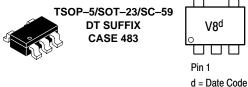


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MARKING DIAGRAMS





	PIN ASSIGNMENT
1	IN B
2	IN A
3	GND
4	OUT Y
5	VCC

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

FUNCTION TABLE

Inp	uts	Output
Α	В	Y
L	L	L
L	Н	Н
н	L	Н
н	Н	L

MAXIMUM RATINGS*

Characteristics	Symbol	Value	Unit
DC Supply Voltage	V _{CC}	-0.5 to +7.0	V
DC Input Voltage	V _{IN}	-0.5 to +7.0	V
DC Output Voltage V _{CC} = 0 High or Low State	V _{OUT}	−0.5 to 7.0 −0.5 to V _{CC} + 0.5	V
Input Diode Current	I _{IK}	-20	mA
Output Diode Current $(V_{OUT} < GND; V_{OUT} > V_{CC})$	I _{OK}	+20	mA
DC Output Current, per Pin	lout	+25	mA
DC Supply Current, V _{CC} and GND	I _{CC}	+50	mA
Power dissipation in still air, SC-88A †	PD	200	mW
Lead temperature, 1 mm from case for 10 s	TL	260	°C
Storage temperature	T _{stg}	-65 to +150	°C

* Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — SC-88A Package: -3 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	V _{CC}	2.0	5.5	V
DC Input Voltage	V _{IN}	0.0	5.5	V
DC Output Voltage	V _{OUT}	0.0	V _{CC}	V
Operating Temperature Range	T _A	-55	+125	°C
Input Rise and Fall Time $\begin{array}{ll} V_{CC}=3.3V\pm0.3V\\ V_{CC}=5.0V\pm0.5V \end{array}$	t _r , t _f	0 0	100 20	ns/V

The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

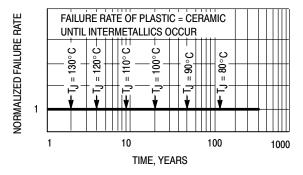


Figure 3. Failure Rate vs. Time Junction Temperature

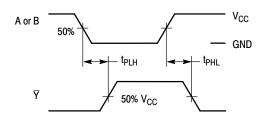
			V _{cc}	ר	A = 25°C	c	T _A ≤	85°C	T _A ≤ 125°C		
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Мах	Min	Max	Min	Max	Unit
V _{IH}	Minimum High–Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V _{IL}	Maximum Low–Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V _{OH} Minimum High–Level Output Voltage V _{IN} = V _{IH} or V _{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu \text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V	
		3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V	
V _{OL}	Maximum Low–Level Output Voltage V _{IN} = V _{IH} or V _{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4mA$ $I_{OL} = 8mA$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μΑ

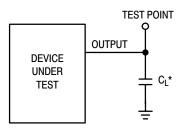
DC ELECTRICAL CHARACTERISTICS

AC ELECTRICAL CHARACTERISTICS ($C_{load} = 50 \text{ pF}$, Input $t_r = t_f = 3.0 \text{ns}$)

				٦	Γ _A = 25°0	C	T _A ≤	85°C	TA ≤ <i>'</i>	125°C	
Symbol Paramete	Parameter	Test Condi	Min	Тур	Мах	Min	Max	Min	Max	Unit	
t _{PLH} , Maximum t _{PHL} Propogation Delay, Input A or B to Y	$V_{CC} = 3.0 \pm 0.3 V$	C _L = 15 pF C _L = 50 pF		4.4 5.7	11.0 14.5		13.0 16.5		15.5 19.5	ns	
	$V_{CC} = 5.0 \pm 0.5 V$	C _L = 15 pF C _L = 50 pF		3.5 4.2	6.8 8.8		8.0 10.0		10.0 12.0		
C _{IN}	Maximum Input Capacitance				5.5	10		10		10	pF
		·				T	ypical @	0 25°C, V	_{CC} = 5.0	DV V	
C _{PD}	Power Dissipation Ca	apacitance (Note 1.)						10			pF

 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.





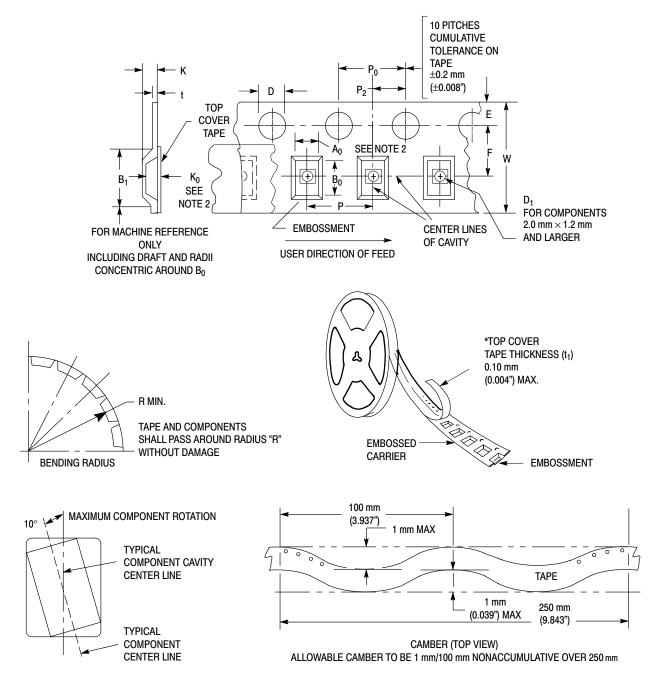
*Includes all probe and jig capacitance

Figure 5. Test Circuit

Figure 4. Switching Waveforms

			Device Nome	nclature				
Device Order Number	Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape & Reel Suffix	Package Type	Tape and Reel Size
MC74VHC1G86DFT2	MC	74	VHC1G	86	DF	T2	SC-88A/ SOT-353 /SC-70	178mm (7") 3000 Unit
MC74VHC1G86DFT4	MC	74	VHC1G	86	DF	T4	SC-88A/ SOT-353 /SC-70	330mm (13") 100000 Unit
MC74VHC1G86DTT1	MC	74	VHC1G	86	DT	T1	TSOP5/ SOT-23 /SC-59	178mm (7") 3000 Unit
MC74VHC1G86DTT3	MC	74	VHC1G	86	DT	T3	TSOP5/ SOT–23 /SC–59	330mm (13") 100000 Unit

DEVICE ORDERING INFORMATION





Tape Size	B ₁ Max	D	D ₁	Е	F	к	Р	P ₀	P ₂	R	т	w
8 mm	4.35 mm (0.171")	1.5 +0.1/ -0.0 mm (0.059 +0.004/ -0.0")	1.0 mm Min (0.039")	1.75 ±0.1 mm (0.069 ±0.004")	3.5 ±0.5 mm (1.38 ±0.002")	2.4 mm (0.094")	4.0 ±0.10 mm (0.157 ±0.004")	4.0 ±0.1 mm (0.156 ±0.004")	2.0 ±0.1 mm (0.079 ±0.002")	25 mm (0.98")	0.3 ±0.05 mm (0.01 +0.0038/ -0.0002")	8.0 ±0.3 mm (0.315 ±0.012")

EMBOSSED	CARRIER	DIMENSIONS	(See Note	s 1	and 2)
LINDOOOLD	OANNEN	DIMILINGIONO		5 1	

1. Metric Dimensions Govern-English are in parentheses for reference only.

2. A₀, B₀, and K₀ are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

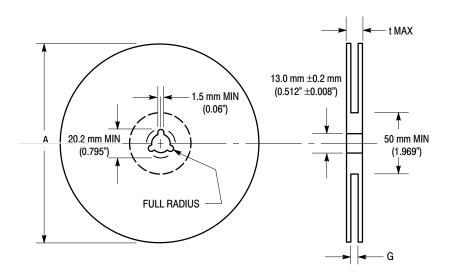
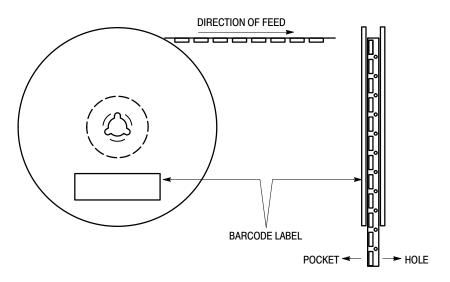


Figure 7. Reel Dimensions

REEL DIMENSIONS

Tape Size	T&R Suffix	A Max	G	t Max
8 mm	T1, T2	178 mm (7")	8.4 mm, +1.5 mm, -0.0 (0.33" + 0.059", -0.00)	14.4 mm (0.56")
8 mm	T3, T4	330 mm (13")	8.4 mm, +1.5 mm, -0.0 (0.33" + 0.059", -0.00)	14.4 mm (0.56")





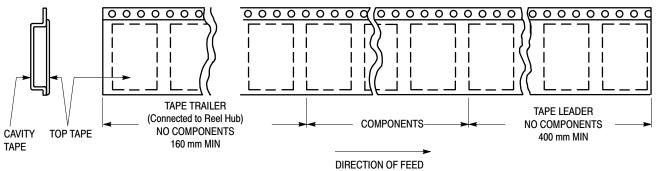
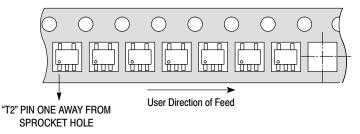
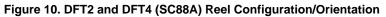


Figure 9. Tape Ends for Finished Goods





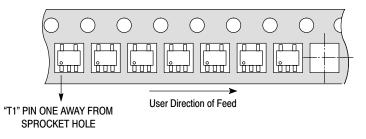
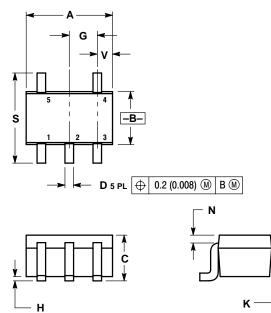


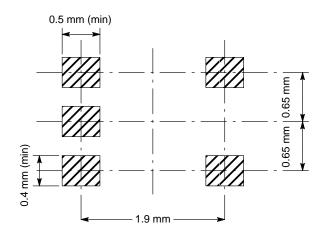
Figure 11. DTT1 and DTT3 (TSOP5) Reel Configuration/Orientation

PACKAGE DIMENSIONS

SC-88A / SOT-353 / SC-70 DF SUFFIX 5-LEAD PACKAGE CASE 419A-01 ISSUE B



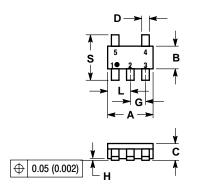
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	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
C	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026	BSC	0.65	BSC	
н		0.004		0.10	
J	0.004	0.010	0.10	0.25	
K	0.004	0.012	0.10	0.30	
Ν	0.008	REF	0.20	REF	
S	0.079	0.087	2.00	2.20	
٧	0.012	0.016	0.30	0.40	1



PACKAGE DIMENSIONS

TSOP-5 / SOT-23 / SC-59 DT SUFFIX 5-LEAD PACKAGE CASE 483-01 ISSUE A

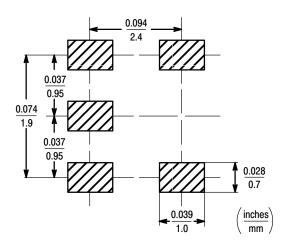
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NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.1142	0.1220
В	1.30	1.70	0.0512	0.0669
C	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.00	0.0335	0.0413
Н	0.013	0.100	0.0005	0.0040
J	0.10	0.26	0.0040	0.0102
Κ	0.20	0.60	0.0079	0.0236
L	1.25	1.55	0.0493	0.0610
М	0 °	10 °	0°	10 °
S	2.50	3.00	0.0985	0.1181



<u>Notes</u>

<u>Notes</u>

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